

Serial No. 10/678,419

July 8, 2005

Reply to the Office Action dated March 8, 2005 and

the Advisory Action dated June 24, 2005

Page 2 of 9

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claim 1 (original): An integrated circuit package comprising:

- a substrate having first and second surfaces and a plurality of conductive traces therebetween;
- a semiconductor die flip-chip mounted to said first surface of said substrate and electrically connected to ones of said conductive traces;
- an intermetallic heat spreader fixed to a back side of said semiconductor die; and
- a plurality of contact balls disposed on said second surface of said substrate, in the form of a ball grid array, ones of said contact balls of said ball grid array being electrically connected with ones of said conductive traces.

Claim 2 (original): The integrated circuit package according to claim 1, wherein said semiconductor die is flip-chip mounted to said first surface of said substrate and electrically connected to ones of said conductive traces via a plurality of solder ball connectors.

Claim 3 (original): The integrated circuit package according to claim 2, further comprising an underfill material surrounding said solder ball connectors.

Claim 4 (original): The integrated circuit package according to claim 1, wherein said solder ball connectors are comprised of eutectic solder.

Claim 5 (original): The integrated circuit package according to claim 1, wherein

Serial No. 10/678,419

July 8, 2005

Reply to the Office Action dated March 8, 2005 and
the Advisory Action dated June 24, 2005

Page 3 of 9

said intermetallic heat spreader is fixed to said back side of said semiconductor die by a thermally conductive adhesive.

Claim 6 (original): The integrated circuit package according to claim 1, wherein said intermetallic heat spreader is fixed to said back side of said semiconductor die by a thermally conductive epoxy.

Claim 7 (original): The integrated circuit package according to claim 1, wherein said intermetallic heat spreader comprises a first portion fixed to said back side of said semiconductor die and a plurality of sidewalls in contact with said substrate.

Claim 8 (original): The integrated circuit package according to claim 7, wherein said sidewalls are fixed to said substrate.

Claim 9 (original): The integrated circuit package according to claim 1, wherein said heat spreader is fixed to a plurality of intermediate sidewalls at a plurality of sites, each of said intermediate sidewalls being fixed to said substrate.

Claim 10 (original): The integrated circuit package according to claim 9, wherein said intermediate sidewalls comprise an intermetallic material.

Claim 11 (original): The integrated circuit package according to claim 1, wherein said intermetallic compound comprises an intermetallic compound having a coefficient of thermal expansion of from about 18 ppm/ $^{\circ}$ C to about 26 ppm/ $^{\circ}$ C.

Claim 12 (original): The integrated circuit package according to claim 1, wherein said intermetallic compound comprises an intermetallic compound having a coefficient

Serial No. 10/678,419

July 8, 2005

Reply to the Office Action dated March 8, 2005 and
the Advisory Action dated June 24, 2005

Page 4 of 9

of thermal expansion of about 22 ppm/°C.

Claim 13 (original): The integrated circuit package according to claim 1, wherein intermetallic compound comprises CuAl₃.

Claim 14 (original): The integrated circuit package according to claim 1, wherein said intermetallic compound has a modulus of elasticity of at least the modulus of elasticity of the semiconductor die.

Claim 15 (original): The integrated circuit package according to claim 1, wherein said intermetallic compound comprises NiAl.

Claim 16 (previously presented): An integrated circuit package comprising:
a substrate having first and second surfaces and a plurality of conductive traces therebetween;
a semiconductor die flip-chip mounted to said first surface of said substrate and electrically connected to ones of said conductive traces;
an intermetallic heat spreader having a coefficient of thermal expansion in the range of about 18 ppm/°C to about 26 ppm/°C, fixed to a back side of said semiconductor die; and
a plurality of contact balls disposed on said second surface of said substrate, in the form of a ball grid array, ones of said contact balls of said ball grid array being electrically connected with ones of said conductive traces; wherein
an intermetallic compound of said intermetallic heat spreader has a modulus of elasticity equal to or greater than a modulus of elasticity of the semiconductor die.

Serial No. 10/678,419

July 8, 2005

Reply to the Office Action dated March 8, 2005 and

the Advisory Action dated June 24, 2005

Page 5 of 9

Claim 17 (original): The integrated circuit package according to claim 16,
wherein the heat spreader has a coefficient of thermal expansion of about 22 ppm/°C.

Claim 18 (canceled).